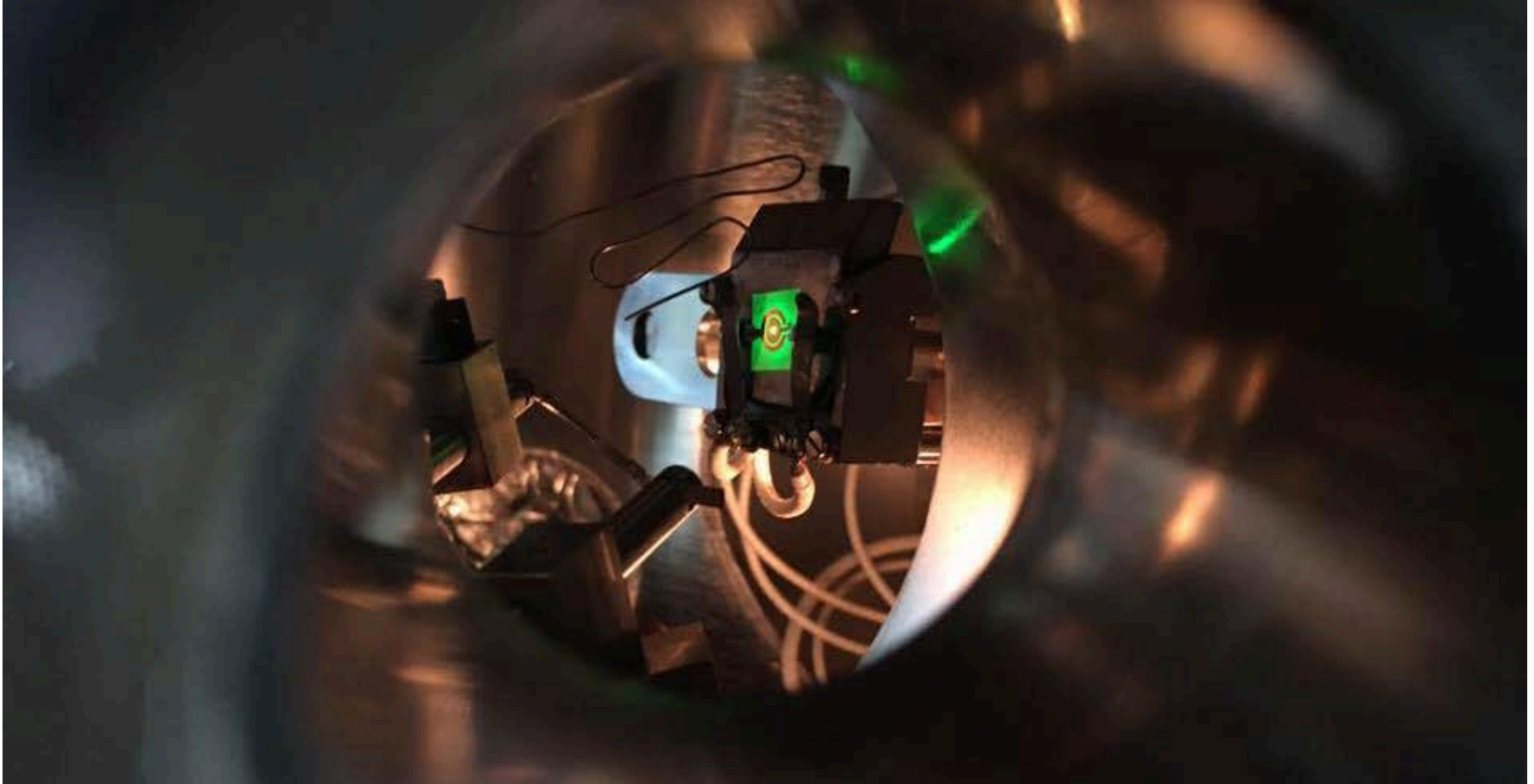


# Identification and Mitigation of Droop Mechanism in GaN-Based Light Emitting Diodes (LEDs)

2017 Building Technologies Office Peer Review



# Project Summary

## Timeline:

Start date: July 31, 2015

Planned end date: July 31, 2017

## Key Milestones

1. Milestone 1.5: 10% quantum yield in photoemission spectroscopy
2. Milestone 3.1: Determination of dominant droop mechanism in blue LEDs
3. Milestone 2.1: Quantification of electron diffusion length in p-GaN

## Budget:

### **Total Project \$ to Date:**

- DOE: \$789,000
- Cost Share: \$157,800

### **Total Project \$:**

- DOE: \$1,000,000
- Cost Share: \$250,000

## Key Partners:

Cree (sample supplier)

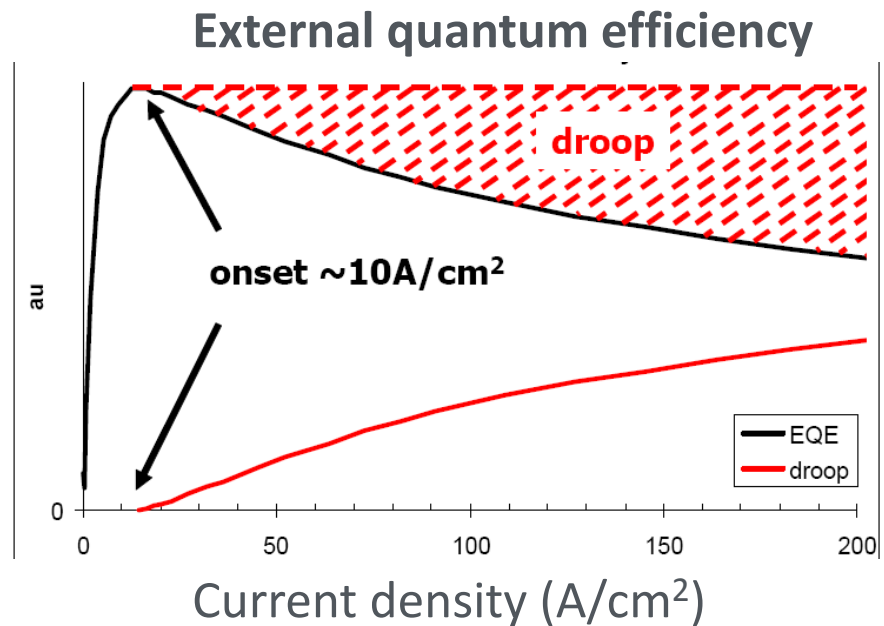
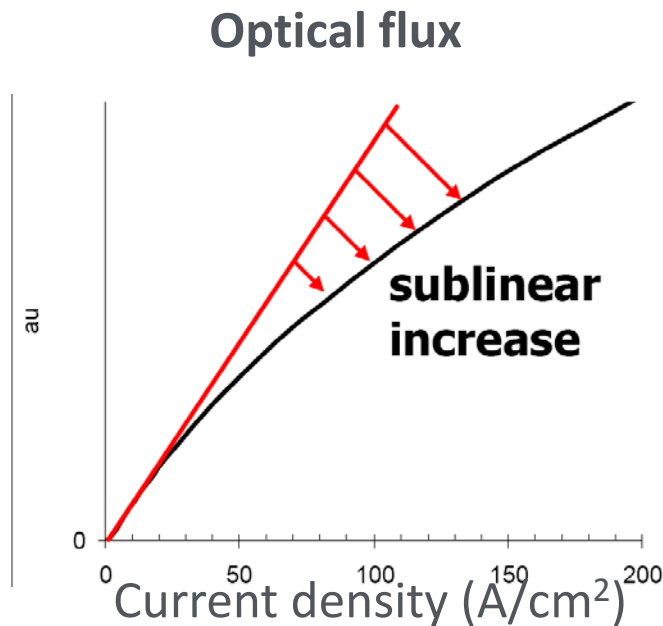
## Project Outcome:

Development of a tool to directly identify the dominant non-radiative recombination mechanisms responsible for current droop, thermal droop, and the green gap in high performance LEDs used for solid state lighting.

From the DOE 2016 Solid State Lighting R&D Plan:  
“**Emitter materials:** addressing current density and thermal droop, green and red efficiency, and red thermal stability.”

From the DOE BTO MYPP:  
“**Core technology R&D** addresses efficiency, performance, and cost targets. Conducted primarily by academia, national laboratories, and research institutions, this work fills technology gaps and significantly advances the knowledge base related to LED and OLED technology”

# Efficiency Droop



## InGaN-based LEDs

- Peak EQE at 1 - 10 A/cm²
- At higher current, LED rapidly lose efficiency
- Independent of color

## Potential Cause: Auger recombination (internal efficiency) $\sim n^3$

- Based on scaling of non-radiative loss - experimental measurement  
[Shen et al. Appl. Phys. Lett. **91** 141101 (2007)]
- First-principles rate indicate Auger recombination may be a significant factor

# Purpose and Objectives

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## **Problem Statement:**

To address the fundamental challenge of identifying the origins of current droop, thermal droop, and the green gap in state-of-the-art LEDs. Understanding the origins of LED *inefficiency* will lead to more efficient LEDs.

## **Target Market and Audience:**

Audience: U.S.-based LED manufacturers and U.S. R&D community.

Target market: U.S. lighting market.

# Purpose and Objectives

## Impact of Project:

### Project's outputs?

Understanding fundamental high current density performance of LEDs  
This understanding will yield new LED designs for more efficient lighting.

### Projects contribution towards program performance and interim market goals?

#### 1 year after project

New active region designs for LEDs for high current density operation

#### 1-3 years after project

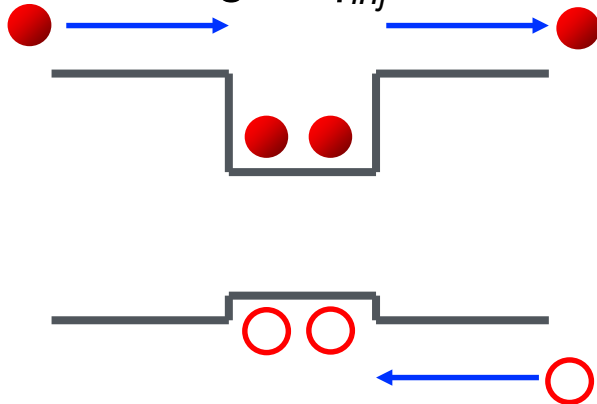
Advanced development of more efficient blue and green LEDs  
for high current density operation

#### 3+ years after project

Mass production of high current density operation LEDs

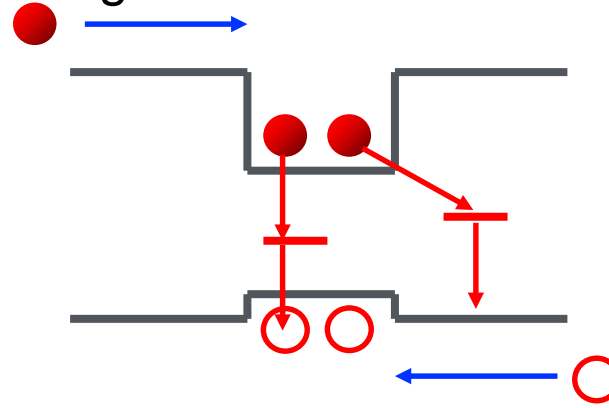
# Approach

Carrier overshoot?  
Changes  $\eta_{inj}$



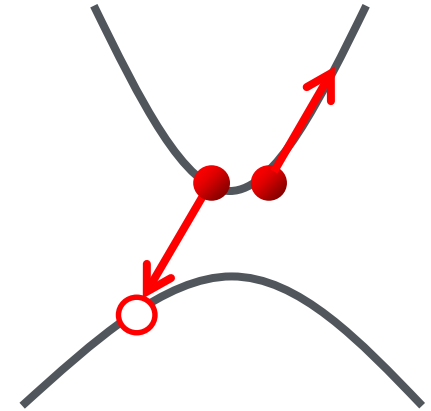
Engineer barrier heights,  
EBL, doping, etc.

Defect activation at  
high current?



Carriers are localized at low  
current, avoiding NR defects

Auger recombination?



Rate  $\sim n^3$   
Diminish carrier density

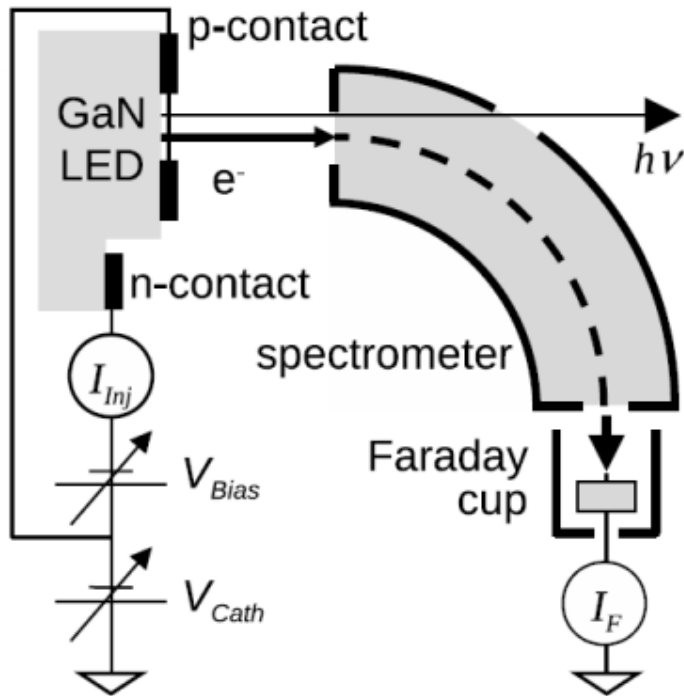
- Based on scaling of nonradiative loss  $\sim n^3$  Auger effect been invoked [Shen 2007]
- But ... other mechanisms can also be fitted. ...
- Increasing active layer volume to decrease carrier density also decreases leakage

**Until recently... *no* hard experimental “signature” for any mechanism**



# Approach

## Low Energy Cylindrical Analyzer



Vary  $V_{Cath}$  to sweep energy

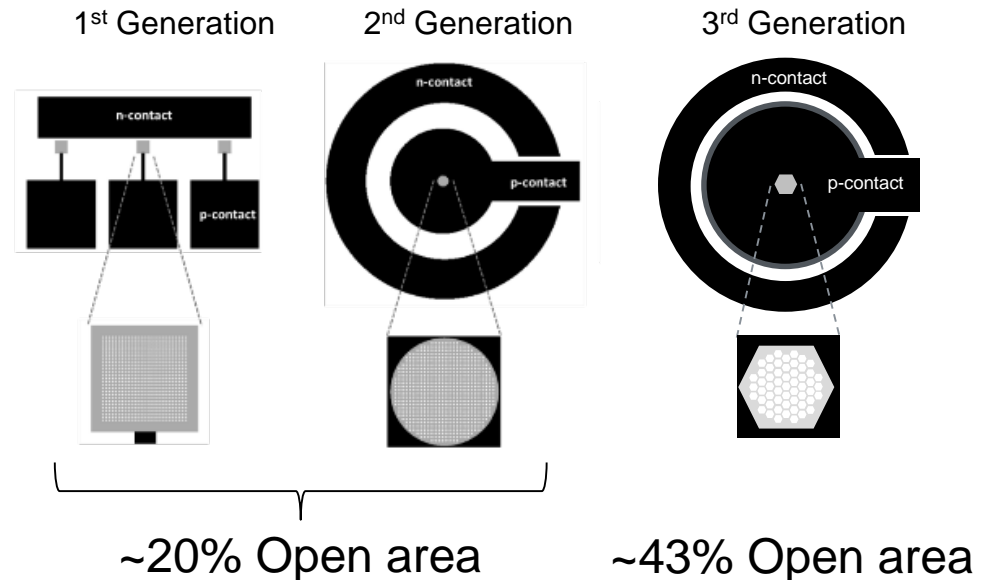
Note:

$V_{Bias}$  relative to  $V_{cath}$

$V_{Bias}$  biased relative to ground

- Constant energy  $\rightarrow$  analyzer potentials fixed
- 50 meV resolution
- $\Phi_{GaN/Cs}$  stable over several days

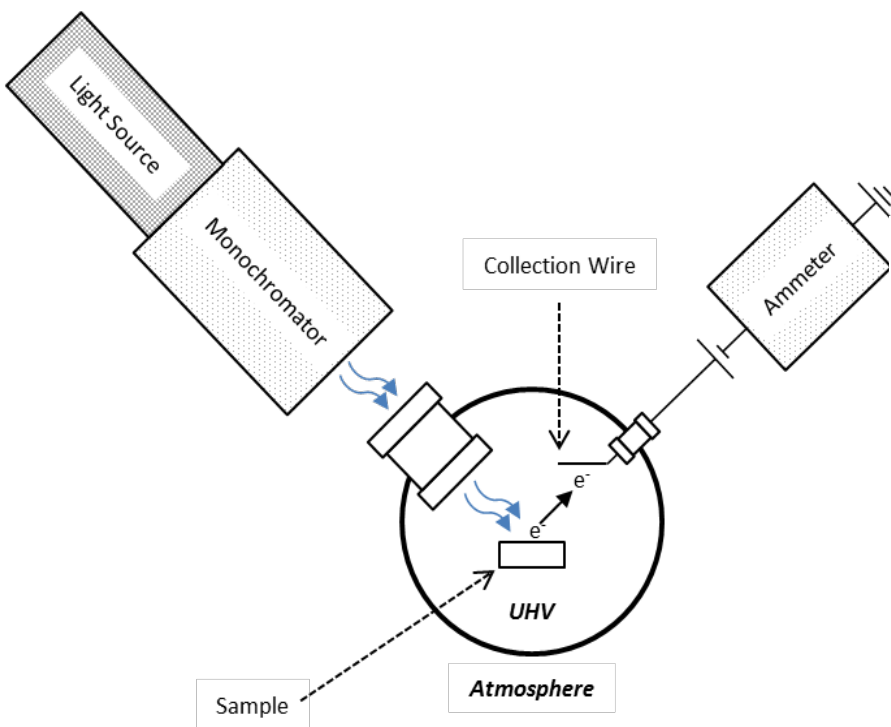
## Device Design





# Progress and Accomplishments

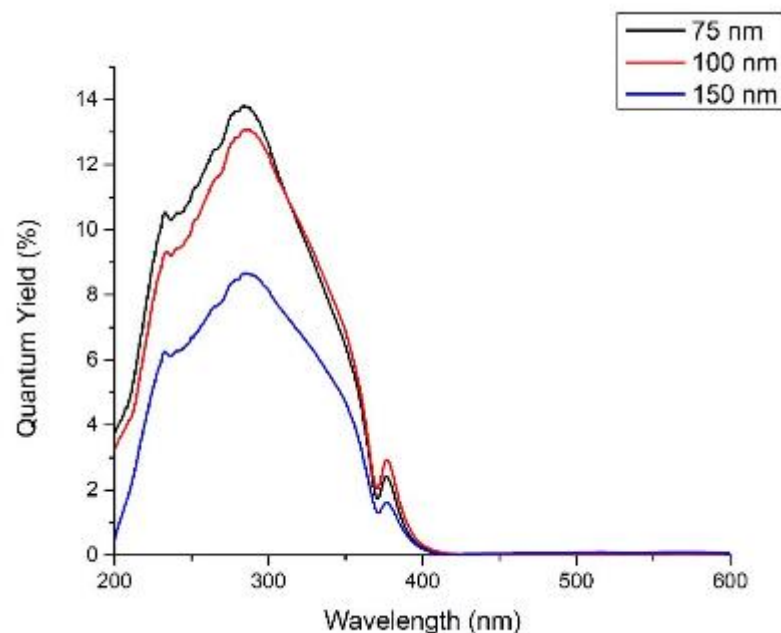
**Milestone 1.5: >10% quantum yield in photoemission spectroscopy from**



## Quantum yield measurement

The total electron current emitted as a function of excitation wavelength with a calibrated source.

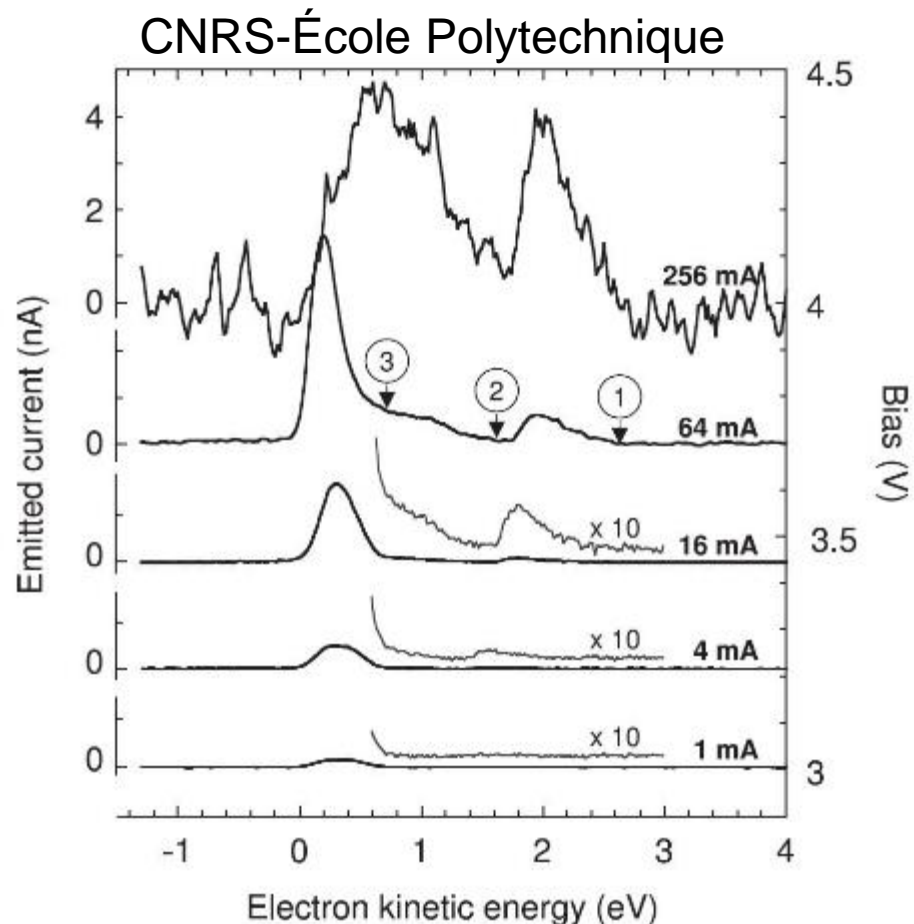
**QY >13% at ~280 nm excitation on p-GaN**



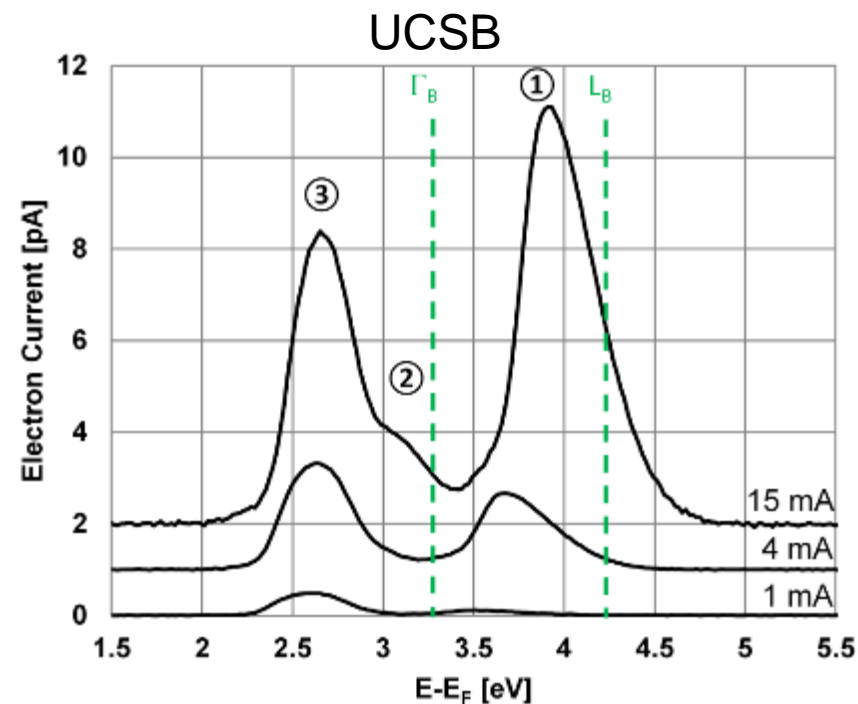
# Progress and Accomplishments

## Subtask 3.1: EES on Commercial Grade Blue: Dominant Droop Mechanisms

UCSB repeats measurements of hot carriers emitted from LEDs.



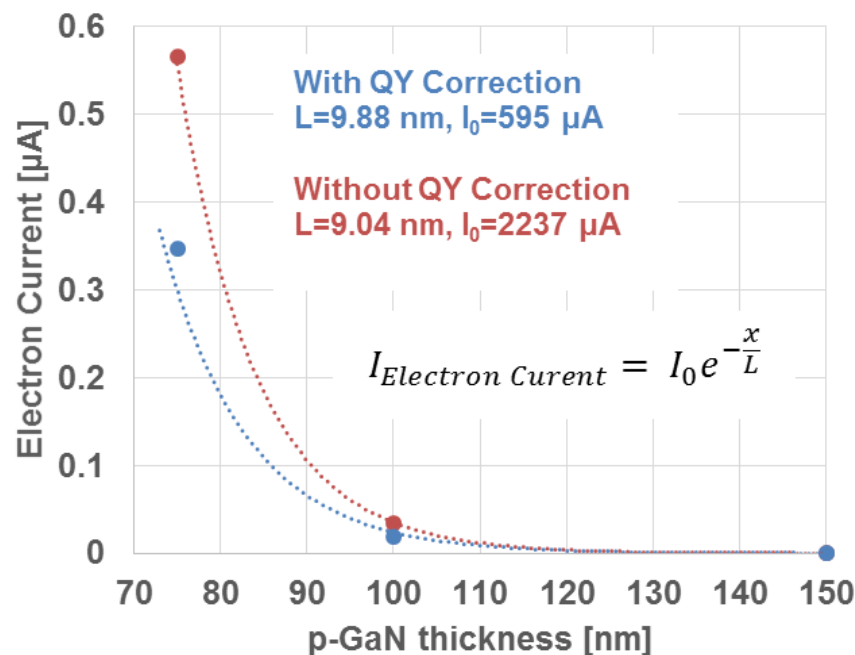
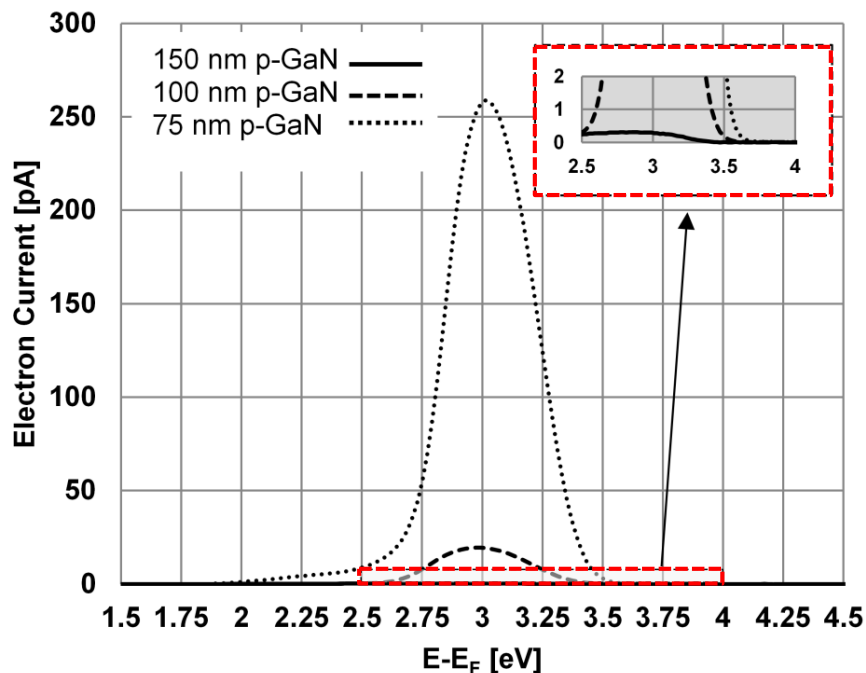
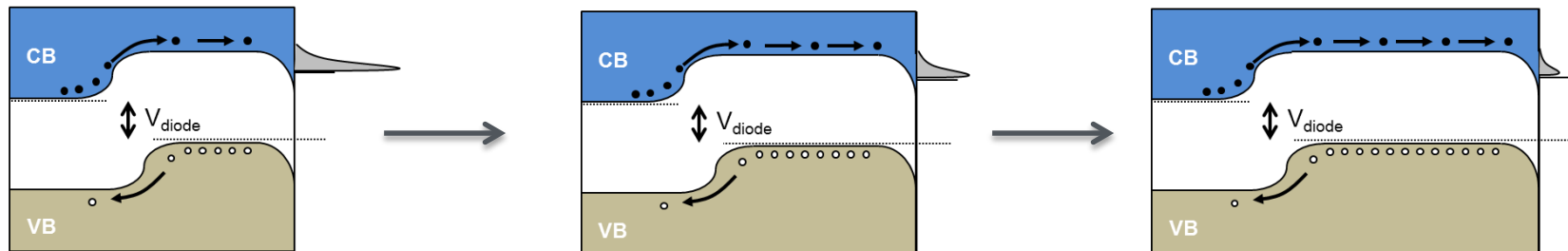
Corrected for analyzer efficiency



Not corrected for analyzer efficiency

# Progress and Accomplishments

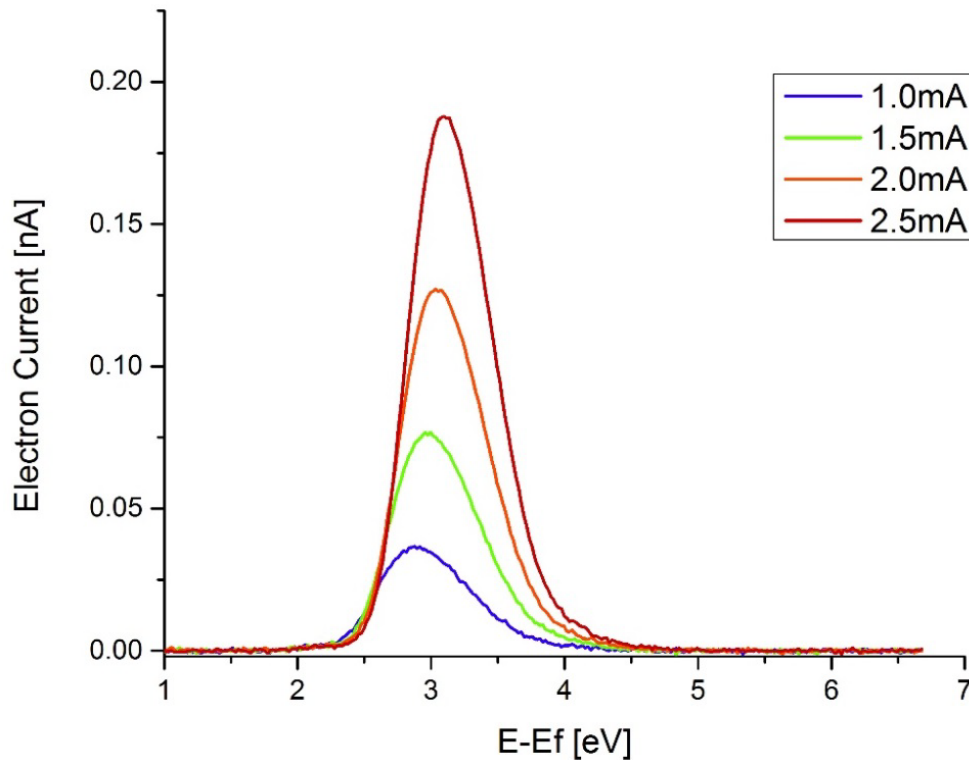
## Milestone 2.1: Quantification of electron diffusion length in p-GaN



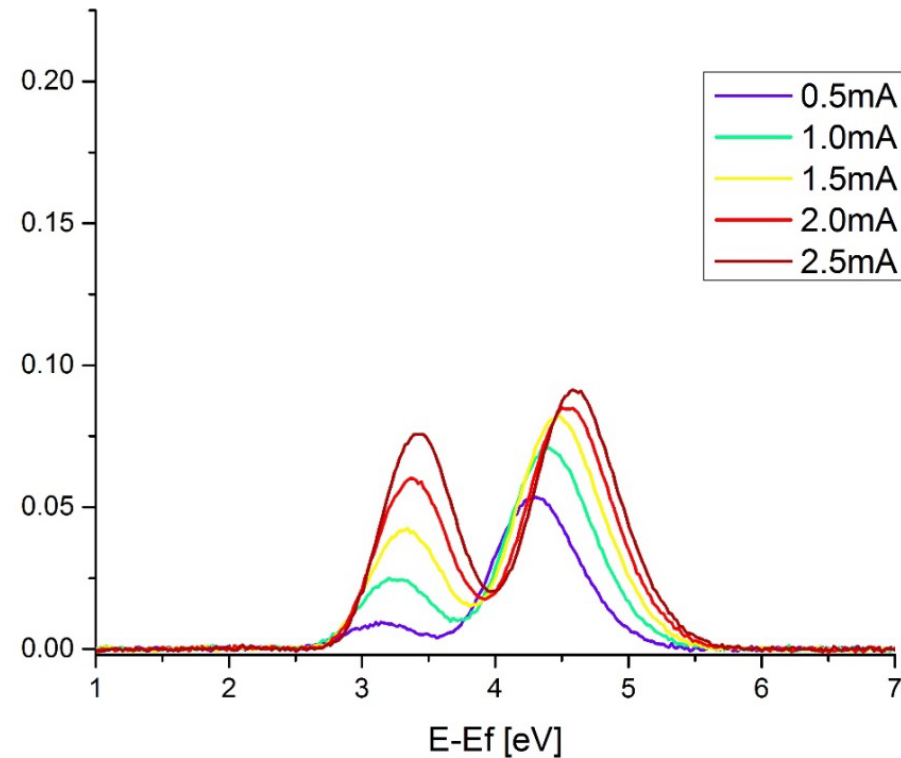
# Progress and Accomplishments

## Milestone 2.2: Quantification of the efficacy of the AlGaN EBL via EE spectroscopy

P-n Junction, no EBL



P-n Junction, with EBL



# Progress and Accomplishments

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## **Market Impact:**

Fundamental understanding of efficiency loss mechanisms enables the engineering solutions which mitigate these physical processes.

Including:

1. Field screening of quantum wells.
2. Semipolar GaN LED substrates.

These solutions allow for increase in quantum well thickness allowing for lower carrier concentration in LED active regions.

# Project Integration and Collaboration

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## **Project Integration:**

Industry partnerships have supplied sample material for the study of state-of-the-art devices. This provides a pathway to understanding efficiency problems which persist in commercially available solid state lighting.

## **Partners, Subcontractors, and Collaborators:**

Cree

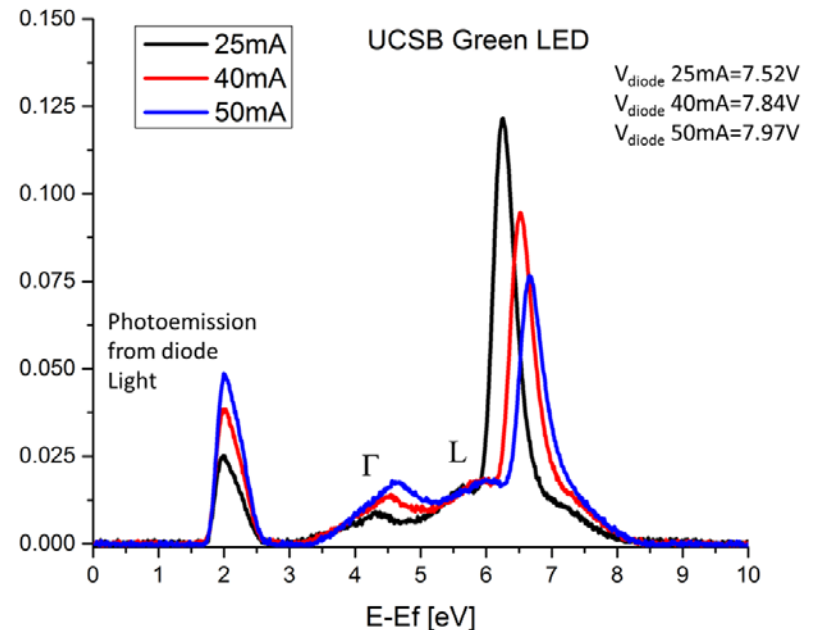
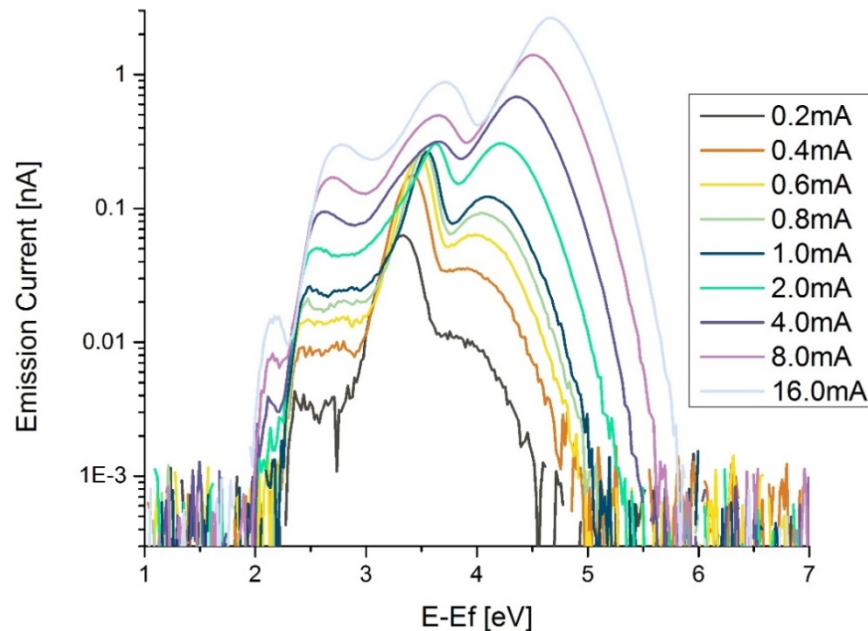
## **Communications:**

DoE SSL workshops

# Next Steps and Future Plans

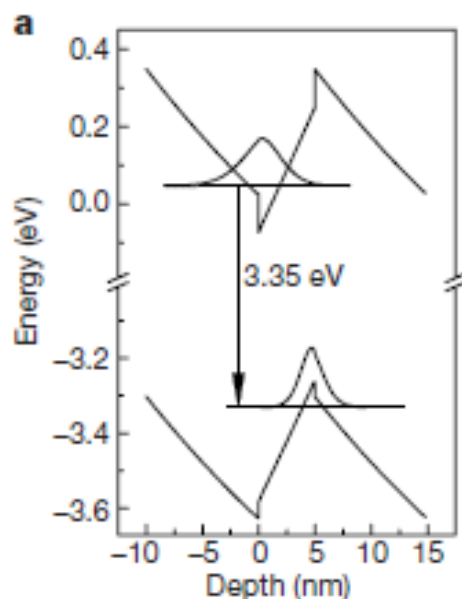
## Milestone 3.2: Determination of dominant droop mechanism in green LEDs

UCSB Green LED

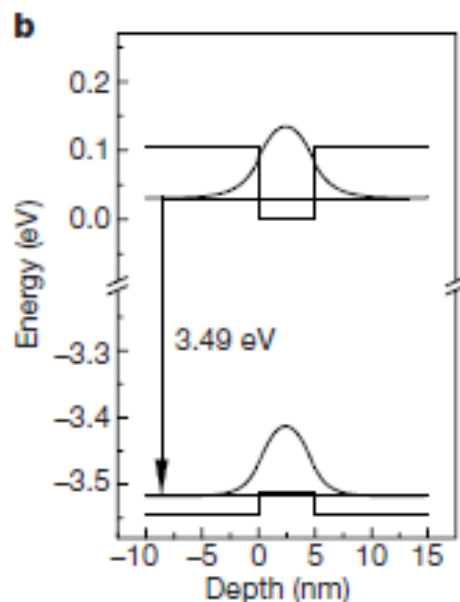


# Next Steps and Future Plans

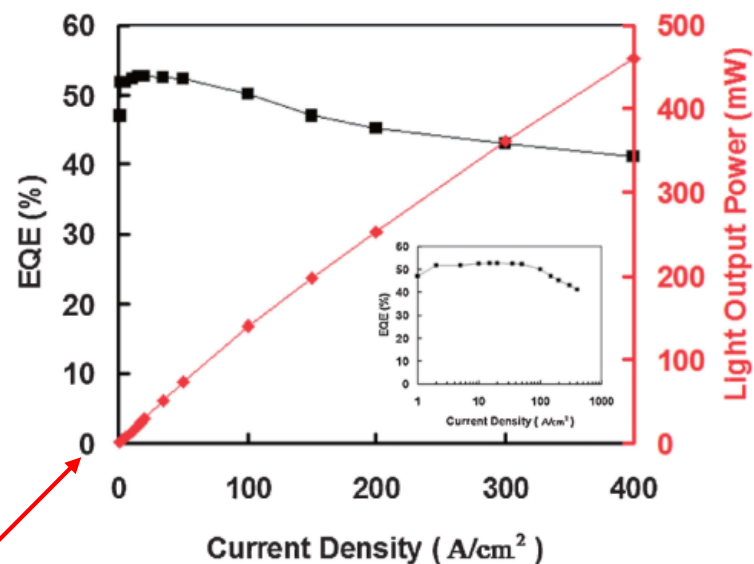
**Milestone 5.2: Identification of residual current droop mechanism in semipolar (202 $\bar{1}\bar{1}$ ) blue LEDs**



c-plane LED



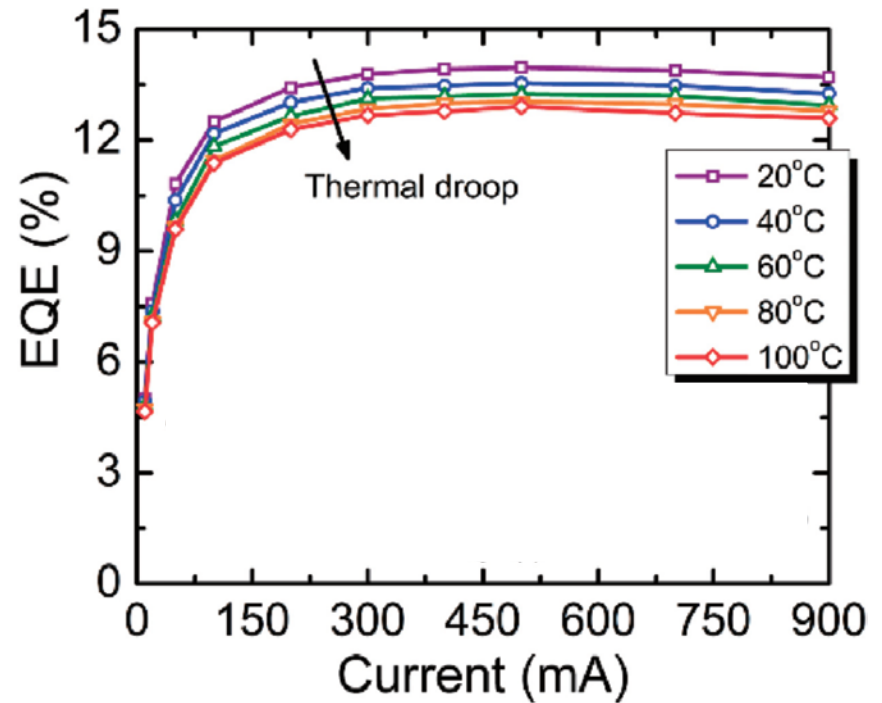
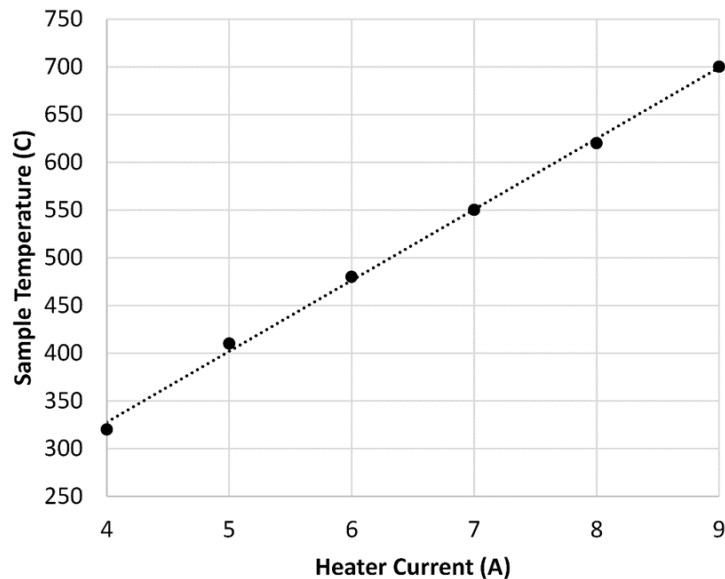
Semipolar LED





# Next Steps and Future Plans

## Milestone 3.3 & 5.4: EES to determine thermal droop mechanisms



# REFERENCE SLIDES

# Project Budget

Spending to Date: 79%

Budget History					
July 31, 2016 – FY 2016 (past)		FY 2017 (current)		FY 2018 (planned)	
DOE	Cost-share	DOE	Cost-share	DOE	Cost-share
\$500,000	\$125,000	\$500,000	\$125,000		

# Project Plan and Schedule

Project Schedule									
Project Start: July 31, 2015		Completed Work							
Projected End: July 31, 2017		Active Task (in progress work)							
		◆	Milestone/Deliverable (Planned)						
		◆	Milestone/Deliverable (Actual)						
		FY2016				FY2017			
Task		Q1 (Oct-Dec)	Q2 (Jan-Mar)	Q3 (Apr-Jun)	Q4 (Jul-Sep)	Q1 (Oct-Dec)	Q2 (Jan-Mar)	Q3 (Apr-Jun)	Q4 (Jul-Sep)
Past Work									
Q1 Milestone 1.1: Annealable ohmic contacts to p-GaN		◆							
Q2 Milestone 1.2: Reduction in metal photoemission via dielectric coating of p-contact			◆						
Q3 Milestone 1.3: 1% quantum yield in photoemission spectroscopy				◆					
Q4 Milestone 1.4: Determination of quantum yields of $\Gamma$ and L valley hot electrons					◆				
Q4 Milestone 2.1: Quantification of electron diffusion length in p-GaN					◆				
Q4 Milestone 2.2: Quantification of the efficacy of the AlGaIn EBL via EE spectroscopy					◆				
Q4 Milestone 3.1: Determination of dominant droop mechanism in blue LEDs					◆				
Q1 Milestone 1.5: 10% quantum yield in photoemission spectroscopy				◆					
Q2 Milestone 1.6: Determination of inter-valley transfer efficiencies						◆			
Current/Future Work									
Q2 Milestone 3.2: Determination of dominant droop mechanism in green LEDs						◆		◆	
Q3 Milestone 1.7: 25% quantum yield in photoemission spectroscopy								◆	
Q3 Milestone 5.2: Identify droop mechanisms in semipolar (20-2- 1) blue LEDs								◆	
Q4 Milestone 5.4: Identify thermal droop mechanisms in semipolar (20-2- 1) blue LEDs									◆
Q4 Milestone 3.3: Determination of dominant thermal droop mechanism in blue LEDs									◆